Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
	184664	ITO (indium near5 tin near5 oxide)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/12 10:41
L2	498053	"GaP" ("P" near5 "GaP") gallium	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/12 10:42
L3	4525	L1 and L2	EPO; JPO; DERWENT	OR	ON	2005/10/12 10:25
			IBM_TDB			
L4	215	L3 and bond\$3	EPO; JPO; DERWENT	OR	ON	2005/10/12 10:42
			; IBM_TDB			
L5	244284	ITO (indium near5 tin near5 oxide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:41
L6	733573	"GaP" ("P" near5 "GaP") gallium	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:42
L7	39093	5 and 6	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:42
L9	15700	7 and bond\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:42
L10	78846	GaAs (gallium near5 arsenide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:45
LII	18995	10 and epitaxial\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:45
L12	1438	11 and epoxy	US-PGPU B; USPAT; USOCR	OR	ON	2005/10/12 10:46